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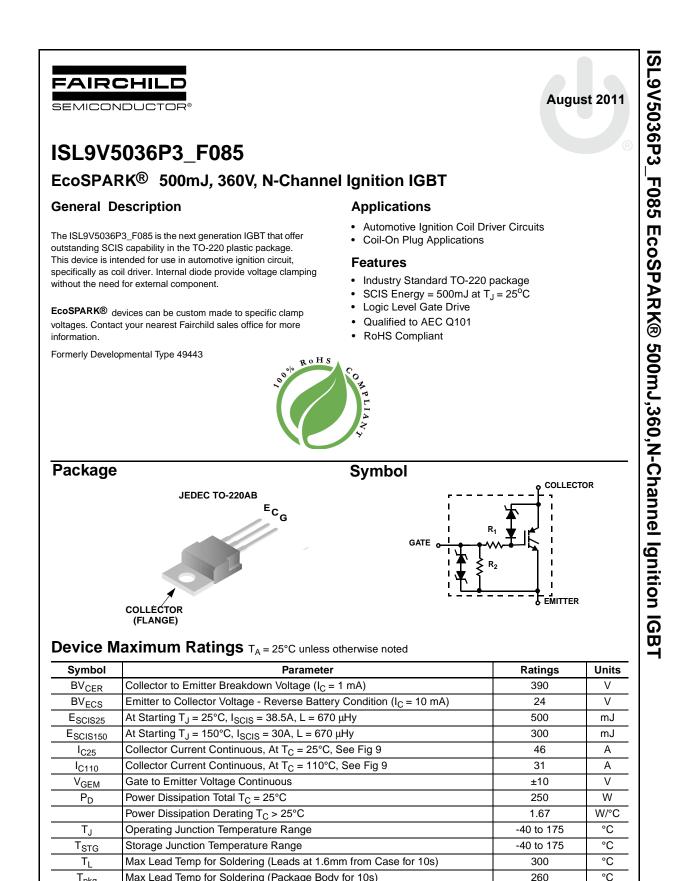


ON Semiconductor®

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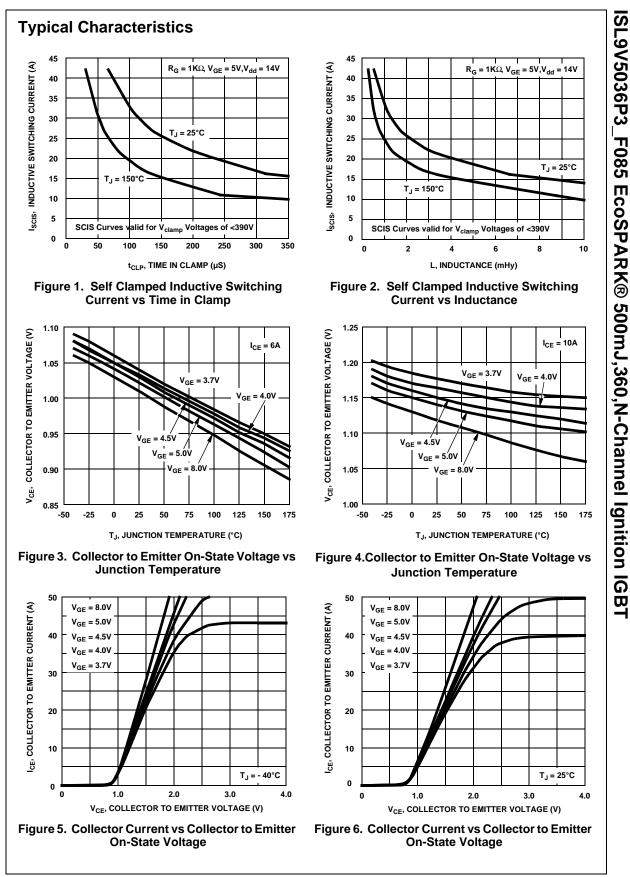
ISL9V5036P3_F085 Rev. C5, August 2011

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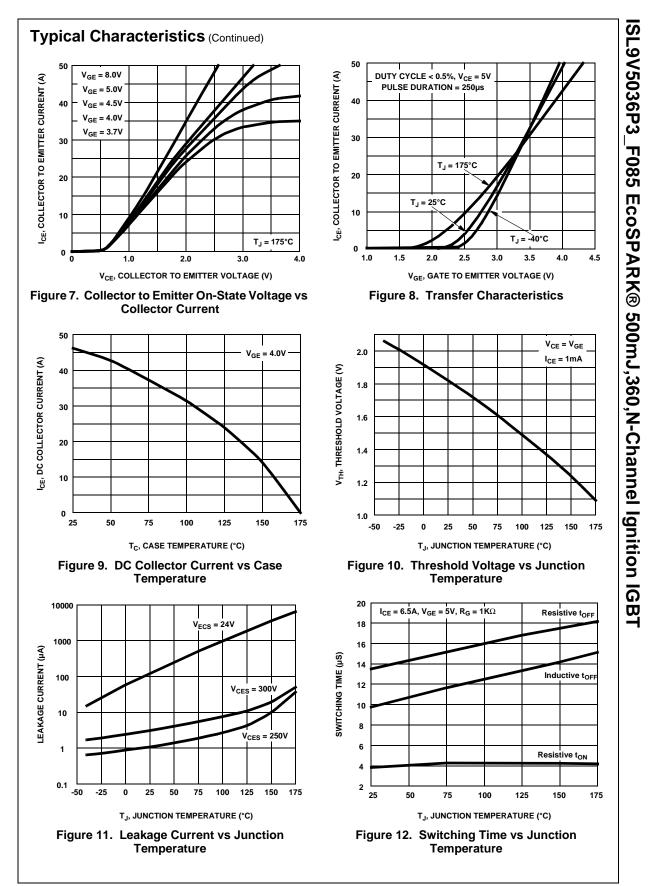
kV

4

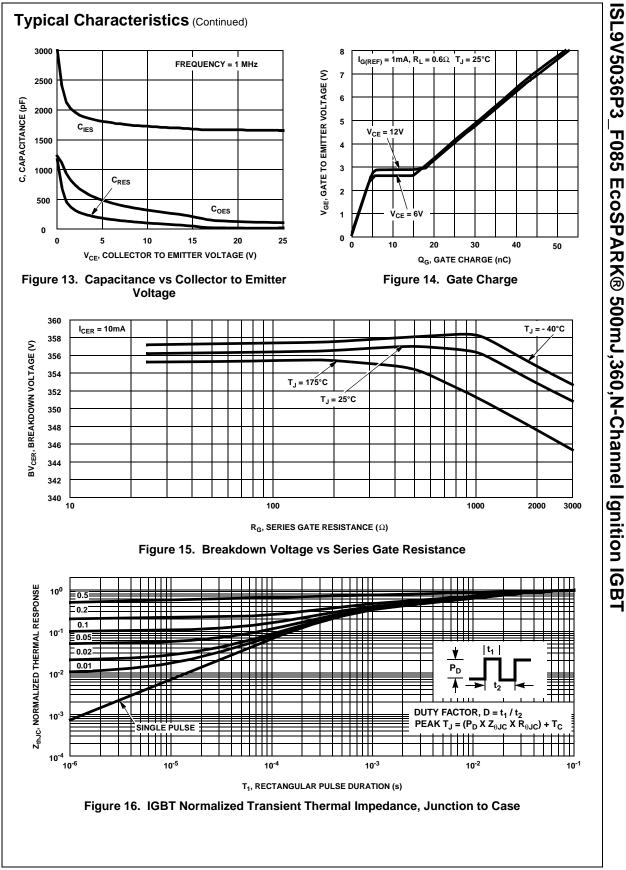
| | Marking | Device | Package | Reel Size | | Tape Width N/A | | Quantity 50 |
|---|--|---|--|---|-------------------------------|-------------------------------------|---------------------------|--|
| V5036P | | ISL9V5036P3_F085 | TO-220AB | Tube | | | | |
| ectric | al Char | acteristics T _A = 25°C un | less otherwise n | oted | | | | |
| Symbol | | Parameter | Test Con | ditions | Min | Тур | Max | Units |
| f State | Characte | eristics | | | | | | |
| BV _{CER} | Collector to Emitter Breakdown Voltage | | I _C = 2mA, V _{GE} | | 330 | 360 | 390 | V |
| | | | $R_G = 1K\Omega$, See Fig. 15 T _J = -40 to 150°C | | | | | |
| BV _{CES} | Collector | to Emitter Breakdown Voltage | $I_{C} = 10mA, V_{GE} = 0,$ $R_{G} = 0, See Fig. 15$ $T_{J} = -40 \text{ to } 150^{\circ}\text{C}$ | | 360 | 390 | 420 | V |
| BV _{ECS} | Emitter to | Collector Breakdown Voltage | $I_{C} = -75mA, V_{GE} = 0V,$ $T_{C} = 25^{\circ}C$ | | 30 | - | - | V |
| BV _{GES} | | mitter Breakdown Voltage | $I_{GES} = \pm 2mA$ | | ±12 | ±14 | - | V |
| I _{CER} | Collector | to Emitter Leakage Current | V _{CER} = 250V, | $T_C = 25^{\circ}C$ | - | - | 25 | μΑ |
| | | | R _G = 1KΩ, See Fig. 11 | T _C = 150°C | - | - | 1 | mA |
| I _{ECS} | Emitter to | Collector Leakage Current | V _{EC} = 24V, See Fig. 11 | | - | - | 1 40 | mA |
| R ₁ | Series Ga | ate Resistance | 1.9.11 | T _C = 150°C | - | - 75 | - 40 | mA Ω |
| R ₂ | | mitter Resistance | | | - 10K | - | - 30K | Ω |
| V _{CE(SAT)} | | to Emitter Saturation Voltage to Emitter Saturation Voltage | $I_{C} = 10A,$ $V_{GE} = 4.0V$ | $T_C = 25^{\circ}C,$ See Fig. 4 $T_C = 150^{\circ}C$ | - | 1.17 1.50 | 1.60 | V |
| V _{CE(SAT)} | Collector | to Emilier Saturation voltage | I _C = 15A, V _{GE} = 4.5V | $1_{\rm C} = 150$ C | - | 1.50 | 1.00 | |
| | | | -GE | | | | | |
| vnamic | Characte | Pristics | GE | I | | | | |
| namic _{Q_{G(ON)}} | Characte Gate Cha | | I _C = 10A, V _{CE} = | = 12V, Fig. 14 | - | 32 | - | nC |
| Q _{G(ON)} | Gate Cha | | $I_{C} = 10A, V_{CE} = V_{GE} = 5V, See$ $I_{C} = 1.0mA,$ | = 12V, Fig. 14 T _C = 25°C | - 1.3 | 32 | - 2.2 | |
| Q _{G(ON)} | Gate Cha | rge | I _C = 10A, V _{CE} = V _{GE} = 5V, See | Fig. 14 | - 1.3 0.75 | 32 | - 2.2 1.8 | nC |
| Q _{G(ON)} | Gate Cha Gate to E | rge | $I_{C} = 10A, V_{CE} = V_{GE} = 5V, See$ $I_{C} = 1.0mA, V_{CE} = V_{GE},$ | Fig. 14 T _C = 25°C | | 32 - - 3.0 | | nC V |
| Q _{G(ON)} V _{GE(TH)} V _{GEP} | Gate Cha Gate to E | rge mitter Threshold Voltage mitter Plateau Voltage | $I_{C} = 10A, V_{CE} = V_{GE} = 5V, See$ $I_{C} = 1.0mA, V_{CE} = V_{GE,}$ See Fig. 10 | Fig. 14 T _C = 25°C T _C = 150°C | 0.75 | - | 1.8 | nC V V |
| Q _{G(ON)} V _{GE(TH)} V _{GEP} vitching | Gate Cha Gate to E Gate to E Gate to E | rge mitter Threshold Voltage mitter Plateau Voltage | $I_{C} = 10A, V_{CE} = V_{GE} = 5V, See$ $I_{C} = 1.0mA, V_{CE} = V_{GE,}$ See Fig. 10 | Fig. 14 $T_{C} = 25^{\circ}C$ $T_{C} = 150^{\circ}C$ $V_{CE} = 12V$ | 0.75 | - | 1.8 | nC V V |
| Q _{G(ON)} V _{GE(TH)} V _{GEP} vitching | Gate Cha Gate to E Gate to E g Charac Current Ti | rge mitter Threshold Voltage mitter Plateau Voltage teristics | $I_{C} = 10A, V_{CE} = V_{GE} = 5V, See$ $I_{C} = 1.0mA, V_{CE} = V_{GE}, See Fig. 10$ $I_{C} = 10A,$ | Fig. 14 $T_{C} = 25^{\circ}C$ $T_{C} = 150^{\circ}C$ $V_{CE} = 12V$ = 1 Ω 1K Ω | 0.75 | 3.0 | - | nC V V V |
| $Q_{G(ON)}$ $V_{GE(TH)}$ V_{GEP} vitching $\frac{t_{d(ON)R}}{t_{rR}}$ | Gate Cha Gate to E Gate to E g Charac Current Ti Current R | rge mitter Threshold Voltage mitter Plateau Voltage teristics | $\begin{split} & I_{C} = 10A, V_{CE} = \\ & V_{GE} = 5V, See \\ & I_{C} = 1.0mA, \\ & V_{CE} = V_{GE}, \\ & See Fig. 10 \\ & I_{C} = 10A, \\ & V_{CE} = 14V, R_{L} = \\ & V_{GE} = 5V, R_{G} = \\ & T_{J} = 25^{\circ}C, See \\ & V_{CE} = 300V, L = \end{split}$ | Fig. 14 $T_{C} = 25^{\circ}C$ $T_{C} = 150^{\circ}C$ $V_{CE} = 12V$ = 1 Ω , 1 $K\Omega$ Fig. 12 = 2mH, | 0.75 | - - 3.0 0.7 | 1.8 - | nC V V V |
| $Q_{G(ON)}$ $V_{GE(TH)}$ V_{GEP} vitching $\frac{t_{d(ON)R}}{t_{rR}}$ | Gate Cha Gate to E Gate to E Current Ti Current R Current Ti | rge mitter Threshold Voltage mitter Plateau Voltage teristics urn-On Delay Time-Resistive tise Time-Resistive | $\begin{split} & I_{C} = 10A, V_{CE} = \\ & V_{GE} = 5V, See \\ & I_{C} = 1.0mA, \\ & V_{CE} = V_{GE}, \\ & See Fig. 10 \\ & I_{C} = 10A, \\ & V_{CE} = 14V, R_{L} = \\ & V_{GE} = 5V, R_{G} = \\ & T_{J} = 25^{\circ}C, See \\ \end{split}$ | Fig. 14 $T_{C} = 25^{\circ}C$ $T_{C} = 150^{\circ}C$ $V_{CE} = 12V$ = 1 Ω 1K Ω Fig. 12 = 2mH, 1K Ω | 0.75 | - - 3.0 0.7 2.1 | 1.8 - 4 7 | nC V V V ν |
| $Q_{G(ON)}$ $V_{GE(TH)}$ V_{GEP} vitching $t_{d(ON)R}$ t_{rR} $t_{d(OFF)L}$ | Gate Cha Gate to E Gate to E Current Ti Current R Current Ti Current Ti Current F | mitter Threshold Voltage mitter Plateau Voltage teristics urn-On Delay Time-Resistive lise Time-Resistive urn-Off Delay Time-Inductive | $\begin{split} & _{C} = 10A, V_{CE} = \\ &V_{GE} = 5V, See \\ & _{C} = 1.0mA, \\ &V_{CE} = V_{GE}, \\ &See Fig. 10 \\ & _{C} = 10A, \\ &V_{CE} = 14V, R_{L} = \\ &V_{GE} = 5V, R_{G} = \\ &T_{J} = 25^{\circ}C, See \\ &V_{CE} = 300V, L = \\ &V_{GE} = 5V, R_{G} = \\ &V_{GE} = 5V, R_{G} = \\ &V_{CE} = \\ &V_{CE} = 5V, R_{C} = \\ &V_{CE} = 5V, R_{C} = \\ &V_{CE} = \\ &V_{CE} = 5V, R_{C} = \\ &V_{CE} =$ | Fig. 14 $T_{C} = 25^{\circ}C$ $T_{C} = 150^{\circ}C$ $V_{CE} = 12V$ = 1 Ω , 1K Ω Fig. 12 = 2mH, 1K Ω Fig. 12 Fig. 12 670 μ H, | 0.75 | - - 3.0 0.7 2.1 10.8 | 1.8 - 4 7 15 | nC V V V V |
| $\begin{array}{c} Q_{G(ON)} \\ \hline V_{GE}(TH) \\ \hline V_{GEP} \\ \hline vitching \\ \hline t_{d(ON)R} \\ \hline t_{rR} \\ \hline t_{d(OFF)L} \\ \hline t_{fL} \\ \hline SCIS \\ \end{array}$ | Gate Cha Gate to E Gate to E Current Ti Current R Current Ti Current Ti Current F | mitter Threshold Voltage mitter Plateau Voltage teristics urn-On Delay Time-Resistive tise Time-Resistive urn-Off Delay Time-Inductive all Time-Inductive uped Inductive Switching | $\begin{split} & _{C} = 10A, V_{CE} = \\ &V_{GE} = 5V, See \\ & _{C} = 1.0mA, \\ &V_{CE} = V_{GE}, \\ &See Fig. 10 \\ & _{C} = 10A, \\ &V_{GE} = 5V, R_{G} = \\ &T_{J} = 25^{\circ}C, See \\ &V_{CE} = 300V, L = \\ &V_{GE} = 5V, R_{G} = \\ &T_{J} = 25^{\circ}C, See \\ &T_{J} = 25^{\circ}C, See \\ &T_{J} = 25^{\circ}C, L = 0 \\ &R_{G} = 1K\Omega, V_{GE} \\ \end{split}$ | Fig. 14 $T_{C} = 25^{\circ}C$ $T_{C} = 150^{\circ}C$ $V_{CE} = 12V$ = 1 Ω , 1K Ω Fig. 12 = 2mH, 1K Ω Fig. 12 Fig. 12 670 μ H, | 0.75 - - - - - | - - 3.0 0.7 2.1 10.8 | 1.8 - 4 7 15 15 | nC V V V ν μs μs μs μs |



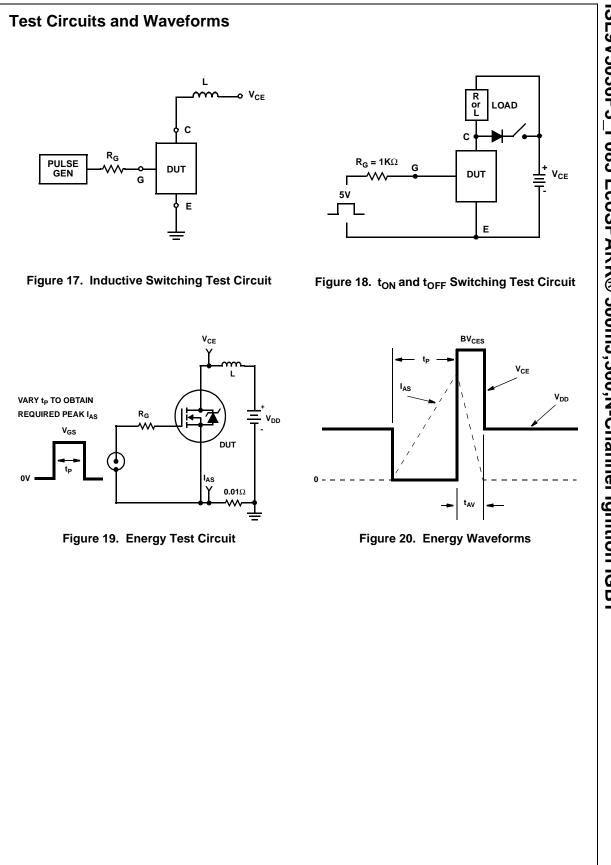
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